Silicon Carbide Schottky Diode

650 V, 30 A

FFSH3065B

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 144 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

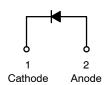
Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



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Schottky Diode



TO-247-2LD CASE 340DA

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code

&3 = Numeric Date Code

kK = Lot Code

FFSH3065B = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSH3065B

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		144	mJ
I _F	Continuous Rectified Forward Current @ T _C < 146°C Continuous Rectified Forward Current @ T _C < 135°C		30	Α
			37	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1100	Α
		T _C = 150°C, 10 μs	1000	Α
I _{F,SM}	Non-Repetitive Forward Surge Current $T_C = 25^{\circ}C$	Half-Sine Pulse, t _p = 8.3 ms	110	А
Ptot	Power Dissipation	T _C = 25°C	268	W
		T _C = 150°C	45	W
T _J , T _{STG}	Operating and Storage Temperature Range TO247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 144 mJ is based on starting $T_{J} = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 24$ A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.56	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 30 A, T _C = 25°C	-	1.38	1.7	V
		I _F = 30 A, T _C = 125°C	-	1.6	2.0	
		I _F = 30 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	0.5	40	μΑ
		V _R = 650 V, T _C = 125°C	-	1	80	
		V _R = 650 V, T _C = 175°C	-	2	160	
Q _C	Total Capacitive Charge	V = 400 V	-	73	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1260	-	pF
		V _R = 300 V, f = 100 kHz	-	115	-	
		V _R = 600 V, f = 100 kHz	_	104	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH3065B	FFSH3065B	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

FFSH3065B

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

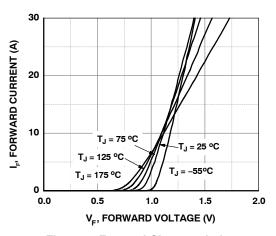


Figure 1. Forward Characteristics

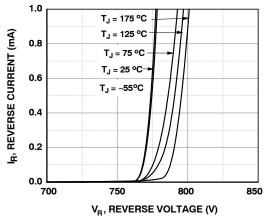


Figure 3. Reverse Characteristics

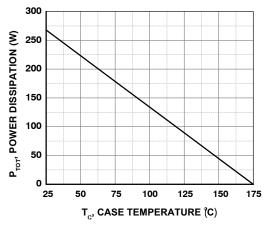


Figure 5. Power Derating

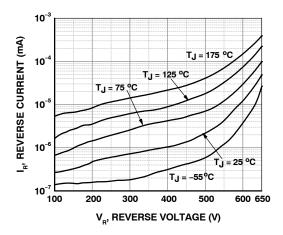


Figure 2. Reverse Characteristics

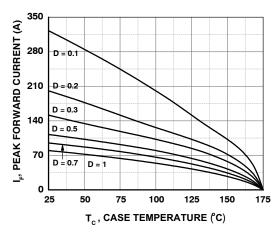


Figure 4. Current Derating

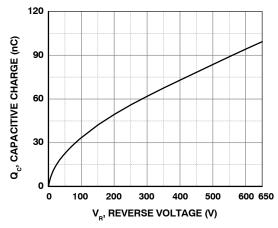
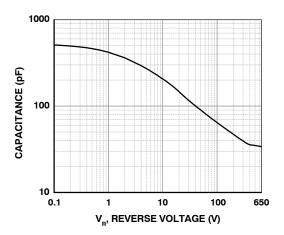


Figure 6. Capacitive Charge vs. Reverse Voltage

FFSH3065B

TYPICAL CHARACTERISTICS

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$



30 C) 10 20 10 0 100 200 300 400 500 600 650 V_R, REVERSE VOLTAGE (V)

Figure 7. Capacitance vs. Reverse Voltage

Figure 8. Capacitance Stored Energy

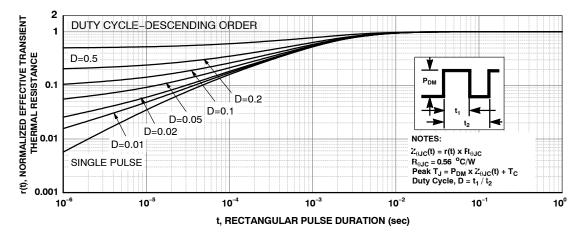
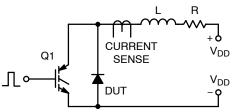


Figure 9. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$$\begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \ \Omega \\ V_{DD} &= 50 \ V \\ EAVL &= 1/2 LI2 \left[V_{R(AVL)} \ / \ (V_{R(AVL)} - V_{DD}) \right] \\ Q1 &= IGBT \ (BV_{CES} > DUT \ V_{R(AVL)}) \end{split}$$



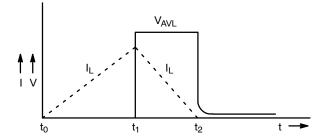
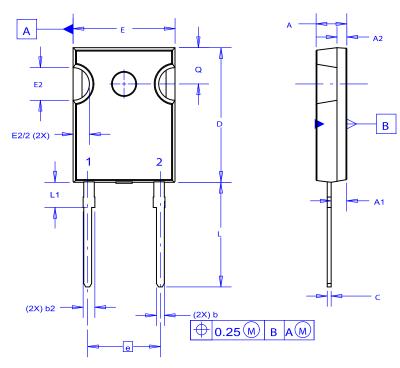


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

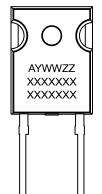
TO-247-2LD CASE 340DA ISSUE A





- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



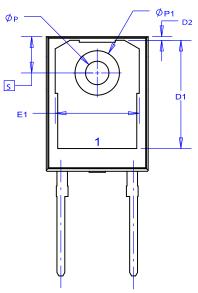
XXXXX = Specific Device Code

A = Assembly Location Y = Year

WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb—Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

DATE 27 FEB 2019



DIM	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A 1	2.20	2.40	2.60	
A2	1.40	1.50	1.60	
b	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	13.08	~	~	
D2	0.51	0.93	1.35	
Е	15.37	15.62	15.87	
E1	12.81	~	~	
E2	4.96	5.08	5.20	
е	?	11.12	?	
L	15.75	16.00	16.25	
L1	3.69	3.81	3.93	
ØΡ	3.51	3.58	3.65	
ØP1	6.60	6.80	7.00	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

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